

IN THE CLAIMS:

Please append claims 140 - 192.

Please amend claims 26 - 28, 30, 35 - 37, 39 - 50, 55 - 56, 59, 63, 72 - 76, 79, 86, 98 - 99, 101, 104 - 105, 111 - 112, 118, 123, 130, and 135.

1 1 - 25. (canceled)

1 26. (Currently amended): A structure comprising an assemblage of
2 separate ~~functional blocks~~electronic devices, each ~~functional block~~electronic device
3 having a first surface and a second surface substantially parallel to said first surface, said
4 ~~functional block~~electronic device further having side surfaces connecting said first
5 surface to said second surface, said first surface having a smaller area than said second
6 surface.

1 27. (Currently amended): The structure of claim 26 wherein said
2 ~~functional block~~electronic device has a ~~maximum linear length~~ dimension of about 50
3 microns or less.

1 28. (Currently amended): The structure of claim 26 wherein said
2 ~~functional block~~electronic device has a trapezoidal cross-section.

1 29. (Previously added): The structure of claim 26 wherein said side
2 surfaces are etched surfaces.

1 30. (Currently amended): The structure of claim 26 wherein said
2 ~~functional block~~electronic device is a multilayered structure.

1 31. (Previously added): The structure of claim 30 wherein said
2 multilayered structure includes a metal layer.

1 32. (Previously added): The structure of claim 30 wherein said
2 multilayered structure includes an insulator layer.

1 33. (Previously added): The structure of claim 30 wherein said
2 multilayered structure includes a layer of silicon dioxide.

1 34. (Previously added): The structure of claim 30 wherein said
2 multilayered structure includes a layer of silicon nitride.

1 35. (Currently amended): The structure of claim 26 wherein said
2 ~~functional block~~electronic device comprises material is selected from the group
3 consisting of silicon, gallium arsenide, aluminum gallium arsenide, diamond, and
4 germanium.

1 36. (Currently amended): The structure of claim 26 wherein said
2 ~~functional block~~electronic device comprises a group III-V compound.

1 37. (Currently amended): The structure of claim 26 wherein said
2 ~~functional block~~electronic device comprises a group II-VI compound.

1 38. (Previously added): The structure of claim 26 wherein the
2 perimeter of said first surface has a rectangular shape, an octagonal shape, or a circular
3 shape.

1 39. (Currently amended): ~~A functional block~~An electronic device
2 comprising semiconductor material and having a tapered profile of a shape generally that
3 ~~of a truncated pyramid~~, said ~~functional block~~electronic device having a maximum linear
4 length dimension of about 50 microns or less less than or equal to 1 mm in measure, said
5 ~~functional block~~electronic device being separated from a substrate.

1 40. (Currently amended): The ~~functional block~~electronic device of
2 claim 39 further having a first surface and a second surface substantially parallel to said
3 first surface.

1 41. (Currently amended): The ~~functional block~~electronic device of
2 claim 40 wherein the perimeter of said first surface has a rectangular shape, an octagonal
3 shape, or a circular shape.

1 42. (Currently amended): The ~~functional block~~electronic device of
2 claim 39 wherein said semiconductor material is a multilayered structure.

1 43. (Currently amended): The ~~functional block~~electronic device of
2 claim 39 wherein said semiconductor material is a group III-V compound.

1 44. (Currently amended): The ~~functional block~~electronic device of
2 claim 43 wherein said semiconductor material is gallium arsenide.

1 45. (Currently amended): The ~~functional block~~electronic device of
2 claim 39 wherein said semiconductor material is a light-emitting diode.

1 46. (Currently amended): The ~~functional block~~electronic device of
2 claim 45 wherein said semiconductor material is a gallium arsenide light-emitting diode.

1 47. (Currently amended): The ~~functional block~~electronic device of
2 claim 39 wherein said semiconductor material is a laser diode.

1 48. (Currently amended): The ~~functional block~~electronic device of
2 claim 39 ~~having wherein a cross-section thereof shows~~ one of a cylindrical shape, a
3 rectangular shape, a square shape, a hexagonal shape, ~~a pyramid shape, a T-shape, and a~~
4 kidney shape.

1 49. (Currently amended): A shaped block of material adapted for being
2 received in a recess of a substrate, said shaped block of material ~~comprising a solid~~
3 having sloped sides and a top surface connected to a bottom surface by said sloped sides,
4 said top surface being substantially parallel to said bottom surface, said top surface being
5 non-congruent with said bottom surface.

1 50. (Currently amended): The shaped block of claim 49 wherein said
2 block of material has a ~~maximum linear dimension of about 50 microns or less~~length
3 measurement less than or equal to 50 microns.

1 51. (Previously added): The shaped block of claim 49 wherein said
2 sloped sides are etched sides.

1 52. (Previously added): The shaped block of claim 49 wherein said
2 sloped sides have a slope greater than about twenty degrees relative to a line normal to
3 said top surface.

1 53. (Previously added): The shaped block of claim 49 wherein said
2 material comprises a multilayered structure.

1 54. (Previously added): The shaped block of claim 49 wherein said
2 material is selected from the group consisting of silicon, gallium arsenide, aluminum
3 gallium arsenide, diamond, and germanium.

1 55. (Currently amended): The shaped block of claim 49 wherein said
2 material ~~is~~comprises a group III - V compound.

1 56. (Currently amended): The shaped block of claim 49 wherein said
2 material ~~is~~comprises a group II - VI compound.

1 57. (Previously added): The shaped block of claim 49 being an optical
2 detector.

1 58. (Previously added): The shaped block of claim 49 wherein the
2 perimeter of said first surface has a rectangular shape, an octagonal shape, or a circular
3 shape.

1 59. (Currently amended): A shaped functional block comprising a
2 semiconductor material and having a shape adapted for self-alignment within a shaped
3 opening-recess formed through a substrate surface, said block having a first surface and a
4 second surface and having etched sides which are sloped such that said block fits into
5 said shaped opening only in an orientation where said first surface is exposed through
6 said substrate surface.

1 60. (Previously added): The functional block of claim 59 wherein said
2 first surface includes a conductive contact disposed thereon.

1 61. (Previously added): The functional block of claim 59 wherein said
2 first surface has an area smaller than said second surface.

1 62. (Previously added): The functional block of claim 61 wherein said
2 first surface has a circular perimeter, a rectilinear perimeter, or an octagonal perimeter.

1 63. (Currently amended): The functional block of claim 59 having a
2 maximum linear-length dimension of about ~~50-microns~~ 1 mm or less.

1 64. (Previously added): The functional block of claim 59 further
2 comprising a multilayered structure.

1 65. (Previously added): The functional block of claim 64 wherein said
2 multilayered structure includes a metal layer.

1 66. (Previously added): The functional block of claim 64 wherein said
2 multilayered structure includes an insulator layer.

1 67. (Previously added): The functional block of claim 64 wherein said
2 multilayered structure includes a layer of silicon dioxide.

1 68. (Previously added): The functional block of claim 64 wherein said
2 multilayered structure includes a layer of silicon nitride.

1 69. (Previously added): The functional block of claim 59 being a light-
2 emitting diode.

1 70. (Previously added): The functional block of claim 59 being a laser
2 diode.

1 71. (Previously added): The functional block of claim 59 being an
2 optical detector.

1 72. (Currently amended): A semiconductor microstructure comprising
2 a ~~wedge-shaped~~shaped block having a first surface substantially parallel to a second
3 surface, said first surface having an associated first area, said second surface having an
4 associated second area, said first area being larger than said second area, an edge adjacent
5 said first surface being sloped, said block having a maximum ~~linear length~~ dimension of
6 about ~~50 microns~~ 1 mm or less in measure.

1 73. (Currently amended): The semiconductor microstructure of claim
2 72 wherein said ~~wedge-shaped~~shaped block comprises material selected from the group
3 consisting of silicon, gallium arsenide, aluminum gallium arsenide, diamond, and
4 germanium.

1 74. (Currently amended): The semiconductor microstructure of claim
2 72 wherein said ~~wedge-shaped~~shaped block comprises a group III-V compound.

1 75. (Currently amended): The semiconductor microstructure of claim
2 72 wherein said ~~wedge-shaped~~shaped block comprises a group II-VI compound.

1 76. (Currently amended): The semiconductor microstructure of claim
2 72 wherein said ~~wedge-shaped~~shaped block is a multilayered structure.

1 77. (Previously added): The semiconductor microstructure of claim 76
2 wherein said multilayered structure constitutes a light-emitting diode.

1 78. (Previously added): The semiconductor microstructure of claim 77
2 wherein said multilayered structure includes gallium arsenide.

1 79. (Currently amended): A portion of an integrated circuit device
2 comprising a shaped functional block ~~separated from a substrate~~, said functional block
3 comprising a semiconductor material and having a ~~maximum linear~~length dimension of
4 ~~about 50 microns or less~~less than or equal to 1 mm in measure, ~~said functional block~~
5 ~~having a wedge-shaped profile~~, said functional block having etched sides.

1 80. (Previously added): The portion of an integrated circuit device of
2 claim 79 wherein said semiconductor material is a multilayered structure.

1 81. (Previously added): The portion of an integrated circuit device of
2 claim 79 wherein said semiconductor material is selected from the group consisting of
3 silicon, gallium arsenide, aluminum gallium arsenide, diamond, and germanium.

1 82. (Previously added): The portion of an integrated circuit device of
2 claim 79 wherein said semiconductor material is a group III-V compound.

1 83. (Previously added): The portion of an integrated circuit device of
2 claim 79 wherein said semiconductor material is a group II-VI compound.

1 84. (Previously added): The portion of an integrated circuit device of
2 claim 79 wherein said semiconductor material constitutes a light-emitting diode.

1 85. (Previously added): The portion of an integrated circuit device of
2 claim 84 wherein said light-emitting diode is a gallium arsenide light-emitting diode.

1 86. (Currently amended): An electronic chip comprising a shaped
2 block of material separated from a substrate and having a first surface and a second
3 surface substantially parallel to said first surface, said block further having etched side
4 surfaces extending from said first surface to said second surface, said first surface having
5 an areal measurement different than an areal measurement of said second surface, said
6 first surface having a conductive contact disposed thereon.

1 87. (Previously added): The electronic chip of claim 86 wherein said
2 block of material has a width of about 50 microns or less and a length of about 50
3 microns or less.

1 88. (Previously added): The electronic chip of claim 86 wherein said
2 etched side surfaces have a slope relative to a line normal to said first surface of greater
3 than about twenty degrees.

1 89. (Previously added): The electronic chip of claim 86 wherein said
2 material comprises a multilayered structure including one or more layers of
3 semiconductor material.

1 90. (Previously added): The electronic chip of claim 89 wherein said
2 multilayered structure includes a silicon layer and a gallium arsenide layer.

1 91. (Previously added): The electronic chip of claim 89 wherein said
2 multilayered structure includes a p-type gallium arsenide layer, an n-type gallium
3 arsenide layer, and a eutectic layer.

1 92. (Previously added): The electronic chip of claim 91 wherein said
2 multilayered structure further includes a silicon substrate layer.

1 93. (Previously added): The electronic chip of claim 86 wherein said
2 material is semiconductor material.

1 94. (Previously added): The electronic chip of claim 86 wherein said
2 electronic chip is a light-emitting diode.

1 95. (Previously added): The electronic chip of claim 86 wherein said
2 electronic chip is a gallium arsenide resonant tunneling diode.

1 96. (Previously added): The electronic chip of claim 86 wherein said
2 electronic chip is a gallium arsenide diode.

1 97. (Previously added): The electronic chip of claim 86 wherein said
2 electronic chip is a gallium arsenide microwave device.

1 98. (Currently amended): The electronic chip of claim 86 ~~having~~
2 wherein a cross-section thereof shows one of a cylindrical shape, a rectangular shape, a
3 square shape, a hexagonal shape, ~~a pyramid shape,~~ a T-shape, and a kidney shape.

1 99. (Currently amended): An electronic chip comprising a shaped
2 functional block including a semiconductor material, said functional block having a
3 ~~wedge shape~~tapered sides with a top surface and a bottom surface smaller than said top
4 surface, said functional block further having a ~~maximum linear dimension of about 50~~
5 ~~microns or less, the length measurement less than or equal to 1 mm,~~ a perimeter of said
6 top surface having a rectilinear shape, a circular shape, or an octagonal shape.

1 100. (Previously added): The electronic chip of claim 99 wherein said
2 top surface is substantially parallel to said bottom surface.

1 101. (Currently amended): The electronic chip of claim 99 further
2 including a conductive contact disposed atop either or both said top surface and said
3 bottom surface.

1 102. (Previously added): The electronic chip of claim 99 wherein said
2 semiconductor material is a multilayered structure.

1 103. (Previously added): The electronic chip of claim 102 wherein said
2 multilayered structure constitutes a light-emitting diode.

1 104. (Currently amended): An electronic component separated from a
2 first substrate comprising:
3 a first surface;
4 a conductive contact disposed atop said first surface;
5 a second surface in substantially parallel relation to said first surface; and
6 etched surfaces connecting said first surface to said second surface,
7 said etched surfaces being ~~in non-parallel relation to one another~~ tapered to
8 define at least a beveled edge adjacent said first surface,
9 wherein said electronic component is adapted for self-alignment within a
10 shaped opening through a surface of a second substrate.

1 105. (Currently amended): The electronic component of claim 104
2 wherein said amount of semiconductor material has a maximum ~~linear dimension~~ length
3 measurement of about 50 microns or less.

1 106. (Previously added): The electronic component of claim 104
2 wherein said etched surfaces are formed by a wet etch process.

1 107. (Previously added): The electronic component of claim 104
2 wherein said etched surfaces are formed by a mask edge.

1 108. (Previously added): The electronic component of claim 104
2 wherein said etched surfaces are formed by a reactive ion etch process.

1 109. (Previously added): The electronic component of claim 104
2 wherein said etched surfaces are formed by an ion milling process.

1 110. (Previously added): The electronic component of claim 104 being
2 a light-emitting diode.

1 111. (Currently amended): A light-emitting diode (LED) comprising a
2 shaped semiconductor block having tapered sides, said semiconductor block comprising a
3 first surface and a second surface in substantially parallel relation to said first surface,
4 said tapered sides defining at least a beveled edge adjacent at least one of said first and
5 second surfaces.

1 112. (Currently amended): The LED of claim 111 wherein said
2 semiconductor block has a ~~maximum linear length~~ dimension of ~~about 50 microns or~~
3 ~~less~~ less than or equal to 50 microns in measure.

1 113. (Previously added): The LED of claim 111 wherein said tapered
2 sides are etched sides.

1 114. (Previously added): The LED of claim 111 incorporated in an
2 active display.

1 115. (Previously added): The LED of claim 111 wherein said
2 semiconductor block is a multilayered structure.

1 116. (Previously added): The LED of claim 115 wherein said
2 multilayered structure includes gallium arsenide.

1 117. (Previously added): The LED of claim 115 wherein said
2 multilayered structure includes a group III-V compound.

1 118. (Currently amended): A light-emitting diode (LED) comprising an
2 amount of semiconductor material, said semiconductor material having a first surface and
3 a second surface smaller than said first surface, said semiconductor material having non-
4 parallel side surfaces connecting said first surface to said second surface, said LED
5 having a ~~maximum linear length~~ dimension of about 50 microns or less than or equal to 1
6 mm.

1 119. (Previously added): The LED of claim 118 wherein said first
2 surface is in substantially parallel relation to said second surface.

1 120. (Previously added): The LED of claim 118 wherein said
2 semiconductor material includes a group III-V compound.

1 121. (Previously added): The LED of claim 120 wherein said
2 semiconductor material includes gallium arsenide.

1 122. (Previously added): The LED of claim 118 wherein the perimeter
2 of said first surface has a rectangular shape, an octagonal shape, or a circular shape.

1 123. (Currently amended): A light-emitting diode (LED) comprising a
2 block of semiconductor material including gallium arsenide, said block having a top
3 surface and a bottom surface connected to said top surface by sloped surfaces, said top
4 and bottom surfaces having different areal measurements, said block having a ~~maximum~~
5 linear dimensionlength measurement of about 50 microns 1 mm or less.

1 124. (Previously added): The LED of claim 123 wherein said sloped
2 surfaces are etched surfaces.

1 125. (Previously added): The LED of claim 124 wherein said etched
2 surfaces are formed by a wet etch process.

1 126. (Previously added): The LED of claim 124 wherein said etched
2 surfaces are formed by a mask edge.

1 127. (Previously added): The LED of claim 124 wherein said etched
2 surfaces are formed by a reactive ion etch process.

1 128. (Previously added): The LED of claim 124 wherein said etched
2 surfaces are formed by an ion milling process.

1 129. (Previously added): The LED of claim 123 wherein the perimeter
2 of said top surface has a rectangular shape, an octagonal shape, or a circular shape.

1 130. (Currently amended): A laser diode comprising a ~~wedge-~~
2 ~~shaped~~shaped block of semiconductor material having a ~~maximum linear length~~
3 dimension of about ~~50 microns~~ 1 mm or less in measure, said block of semiconductor
4 having a tapered edge.

1 131. (Previously added): The laser diode of claim 130 wherein said
2 semiconductor material comprises a group III-V compound.

1 132. (Previously added): The laser diode of claim 131 wherein said
2 semiconductor material comprises gallium arsenide.

1 133. (Previously added): The laser diode of claim 130 wherein said
2 block comprises first and second surfaces in parallel relation and etched side surfaces
3 connecting said first and second surfaces, said first surface having an area different than
4 an area of said second surface.

1 134. (Previously added): The laser diode of claim 130 incorporated in
2 an optical data channel.

1 135. (Currently amended): An optical detector comprising a ~~wedge-~~
2 ~~shaped~~shaped block of semiconductor material having a ~~maximum linear~~
3 ~~dimension~~length measurement of about ~~50 microns~~1 mm or less, said block of
4 semiconductor material having a beveled edge adjacent a major surface thereof.

1 136. (Previously added): The optical detector of claim 135 wherein said
2 semiconductor material comprises a group III-V compound.

1 137. (Previously added): The optical detector of claim 136 wherein said
2 semiconductor material comprises gallium arsenide.

1 138. (Previously added): The optical detector of claim 135 wherein said
2 block comprises first and second surfaces in parallel relation and etched side surfaces
3 connecting said first and second surfaces, said first surface having an area different than
4 an area of said second surface.

1 139. (Previously added): The optical detector of claim 135 incorporated
2 in an optical data channel.

1 140. (New): The structure of claim 26 wherein said electronic device
2 has a length dimension of about 1 mm or less.

1 141. (New): The structure of claim 26 wherein said electronic device
2 has a length dimension of about 500 microns or less.

1 142. (New): The structure of claim 26 wherein said electronic device
2 has an edge portion that is beveled.

1 143. (New): The structure of claim 26 wherein said electronic device is
2 shaped like a truncated pyramid.

1 144. (New): The electronic device of claim 39 wherein said length
2 dimension less than or equal to 500 microns.

1 145. (New): The electronic device of claim 39 wherein said length
2 dimension is less than or equal to 50 microns.

1 146. (New): The electronic device of claim 39 wherein said profile has
2 a trapezoidal shape.

1 147. (New): The electronic device of claim 39 wherein said profile
2 shows at least a partially beveled edge.

1 148. (New): The electronic device of claim 39 having one of a pyramid
2 shape and a truncated pyramid shape.

1 149. (New): The shaped block of claim 49 wherein said block of
2 material has a length measurement less than or equal to 500 microns.

1 150. (New): The shaped block of claim 49 wherein said block of
2 material has a length measurement less than or equal to 1 mm.

1 151. (New): The shaped block of claim 49 wherein said sloped sides
2 have a trapezoidal profile.

1 152. (New): The shaped block of claim 49 wherein said sloped sides
2 define a portion of a beveled edge.

1 153. (New): The shaped block of claim 49 wherein said shaped block
2 has a shape of a truncated pyramid.

1 154. (New): The functional block of claim 59 having a maximum length
2 dimension of about 500 micron or less.

1 155. (New): The functional block of claim 59 having a maximum length
2 dimension of about 50 micron or less.

1 156. (New): The functional block of claim 59 wherein said etched sides
2 are characterized by having a trapezoidal profile.

1 157. (New): The functional block of claim 59 wherein said etched sides
2 form a beveled edge adjacent said first surface.

1 158. (New): The functional block of claim 59 having a shape of a
2 truncated pyramid.

1 159. (New): The semiconductor microstructure of claim 72 wherein said
2 length dimension further is about 500 microns or less in measure.

1 160. (New): The semiconductor microstructure of claim 159 wherein
2 said length dimension further is about 50 microns or less in measure.

1 161. (New): The semiconductor microstructure of claim 72 wherein said
2 edge has a trapezoidal profile.

1 162. (New): The semiconductor microstructure of claim 72 wherein said
2 edge is beveled.

1 163. (New): The semiconductor microstructure of claim 72 wherein said
2 shaped block has a truncated pyramid appearance.

1 164. (New): The portion of an integrated circuit device of claim 79
2 wherein said length dimension further is less than or equal to 500 microns in measure.

1 165. (New): The portion of an integrated circuit device of claim 164
2 wherein said length dimension further is less than or equal to 50 microns in measure.

1 166. (New): The portion of an integrated circuit device of claim 79
2 wherein said etched sides have a form a trapezoidal profile.

1 167. (New): The portion of an integrated circuit device of claim 79
2 wherein said functional block further comprises a first major surface and a second major
3 surface connected to said first major surface by said etched sides, a portion of said etched
4 sides adjacent to said first major surface forming a beveled edge.

1 168. (New): The portion of an integrated circuit device of claim 79
2 wherein said functional block has a shape of a truncated pyramid.

1 169. (New): The electronic chip of claim 86 wherein said block of
2 material has a width of about 1 mm or less and a length of about 1 mm or less.

1 170. (New): The electronic chip of claim 86 wherein said block of
2 material has a width of about 500 microns or less and a length of about 500 microns or
3 less.

1 171. (New): The electronic chip of claim 86 wherein said shaped block
2 has an outwardly sloped profile.

1 172. (New): The electronic chip of claim 86 wherein said shaped block
2 has an inwardly sloped profile.

1 173. (New): The electronic chip of claim 86 wherein a profile of said
2 shaped block resembles a trapezoid.

1 174. (New): The electronic chip of claim 86 wherein said etched side
2 surfaces define a beveled edge adjacent said first surface.

1 175. (New): The electronic chip of claim 86 wherein said shaped block
2 is one of a pyramid shape and a truncated pyramid shape.

1 176. (New): The electronic chip of claim 99 wherein said length
2 measurement further is less than or equal to 500 microns.

1 177. (New): The electronic chip of claim 176 wherein said length
2 measurement further is less than or equal to 50 microns.

1 178. (New): The electronic chip of claim 99 wherein said tapered sides
2 define at least a beveled edge adjacent said top surface.

1 179. (New): The electronic component of claim 104 wherein said
2 amount of semiconductor material has a maximum length measurement of about 1 mm or
3 less.

1 180. (New): The electronic component of claim 104 wherein said
2 amount of semiconductor material has a maximum length measurement of about 500
3 microns or less.

1 181. (New): The LED of claim 111 wherein said semiconductor block
2 has a length dimension less than or equal to 1 mm in measure.

1 182. (New): The LED of claim 111 wherein said semiconductor block
2 has a length dimension less than or equal to 500 microns in measure.

1 183. (New): The LED of claim 118 wherein said length dimension
2 further is less than or equal to 500 microns.

1 184. (New): The LED of claim 183 wherein said length dimension
2 further is less than or equal to 50 microns.

1 185. (New): The LED of claim 118 further comprising a beveled edge
2 formed adjacent one of said first and second surfaces.

1 186. (New): The LED of claim 123 wherein said length measurement
2 further is about 500 microns or less.

1 187. (New): The LED of claim 186 wherein said length measurement
2 further is about 50 microns or less.

1 188. (New): The LED of claim 124 wherein said sloped surfaces define
2 a beveled edge adjacent one of said top and bottom surfaces.

1 189. (New): A shaped block of semiconductor material having tapered
2 sides, said block of material comprising a first surface and a second surface in
3 substantially parallel relation to said first surface, said tapered sides defining a beveled
4 edge adjacent at least one of said first and second surfaces.

1 190. (New): The shaped block of claim 189 having a maximum length
2 dimension less than or equal to 1 mm in measure.

1 191. (New): The shaped block of claim 189 having a maximum length
2 dimension less than or equal to 500 microns in measure.

1 192. (New): The shaped block of claim 189 having a maximum length
2 dimension less than or equal to 50 microns in measure.

REMARKS

Claims 26 - 192 are pending.

Fifteen sets of claims are pending. For convenience, each set of claims has been identified. For each set of claims, the first listed claim is the independent claim (shown in bold) and the remaining listed claims consist of claims depending from the independent claim:

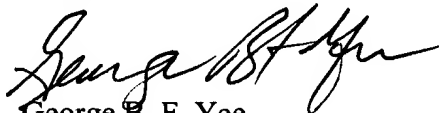
claim set 1: **26**, 27 - 38 and 140 - 143;
claim set 2: **39**, 40 - 48 and 144 - 148;
claim set 3: **49**, 50 - 58 and 149 - 153;
claim set 4: **59**, 60 - 71 and 154 - 158;
claim set 5: **72**, 73 - 78 and 159 - 163;
claim set 6: **79**, 80 - 85 and 164 - 168;
claim set 7: **86**, 87 - 98 and 169 - 175;
claim set 8: **99**, 100 - 103 and 176 - 178;
claim set 9: **104**, 105 - 110 and 179 - 180;
claim set 10: **111**, 112 - 117 and 181 - 182;
claim set 11: **118**, 119 - 122 and 183 - 185;
claim set 12: **123**, 124 - 129 and 186 - 188;
claim set 13: **130**, 131 - 134;
claim set 14: **135**, 136 - 139; and
claim set 15: **189**, 190 - 192.

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The pending claims are believed to be allowable. The issuance of a formal Notice of Allowance at an early date is respectfully requested. If the Examiner believes a telephone conference would expedite prosecution of this application, please telephone the undersigned at 650-326-2400.

Respectfully submitted,



George B. F. Yee
Reg. No. 37,478

TOWNSEND and TOWNSEND and CREW LLP
Two Embarcadero Center, 8th Floor
San Francisco, California 94111-3834
Tel: (650) 326-2400
Fax: (415) 576-0300
GBFY:dhe
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